

In the Claims:

- 1 1. (original) A process for the fabrication of isolation
2 structures with the following process steps
3 • provision of a semiconductor substrate (11),
4 • forming of at least two trenches (12) spaced from each
5 other in the semiconductor substrate (11) with at
6 least one rib (13) positioned between the trenches
7 (12),
8 • conversion of the substrate material in the area of
9 the trenches (12) into an electrically insulating
10 material (14) up to the complete conversion of the rib
11 or the ribs (13) arranged between them,
12 • forming of a functional structure (15) within the
13 substrate material which is mechanically connected
14 with the substrate exclusively by means of the
15 converted substrate material which is formed at the
16 trenches.
- 1 2. (original) A process according to patent claim 1
2 characterised in that silicon is used as semiconductor
3 substrate.
- 1 3. (original) A process according to patent claim 2
2 characterised in that the substrate material is converted
3 by means of thermal oxidation.

Claims 4, 5, 6 (canceled).

[REMARKS FOLLOW ON NEXT PAGE]